



YJQ016NP04A

NMOS Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						



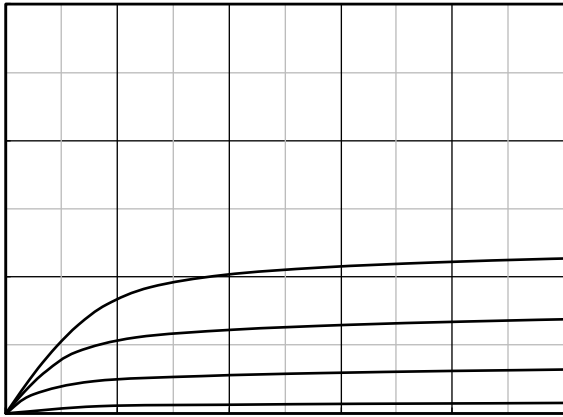
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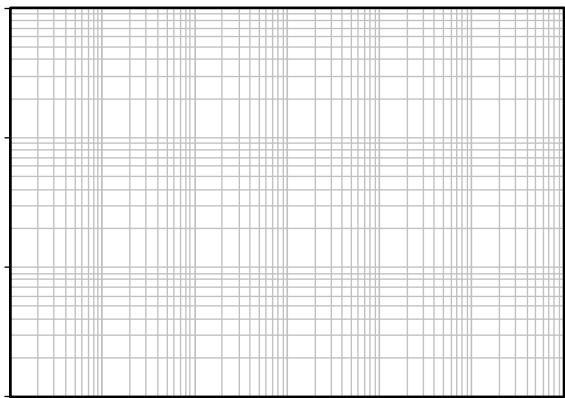
PMOS Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
		$V_{DS}=-40V, V_{GS}=0V, T_J=150$	-	-	-100	



NMOS Typical Electrical and Thermal Characteristics Diagrams





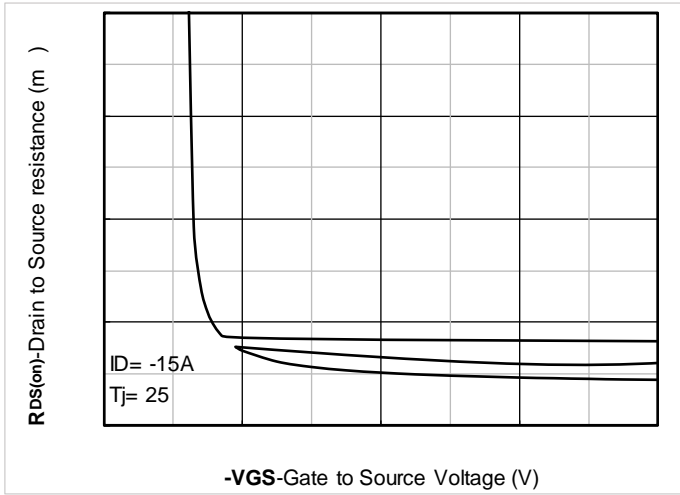


Figure 5. On-Resistance vs Gate to Source Voltage

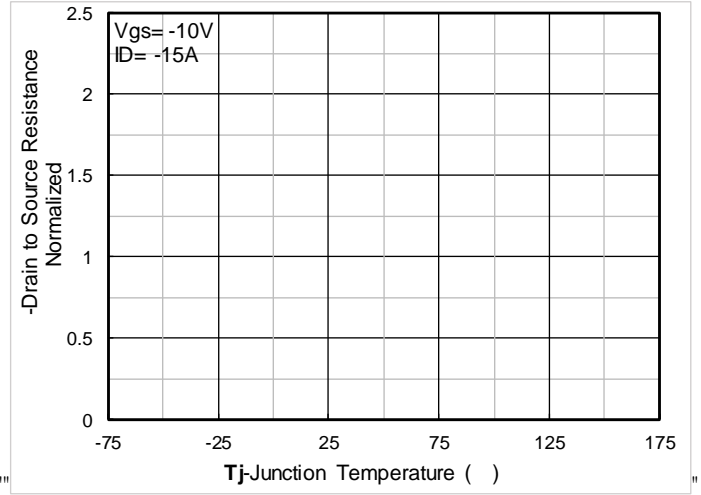
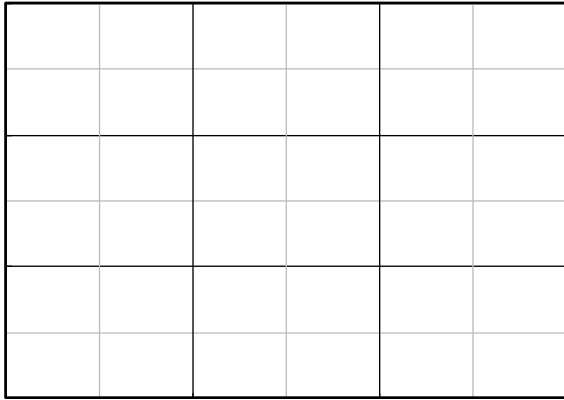
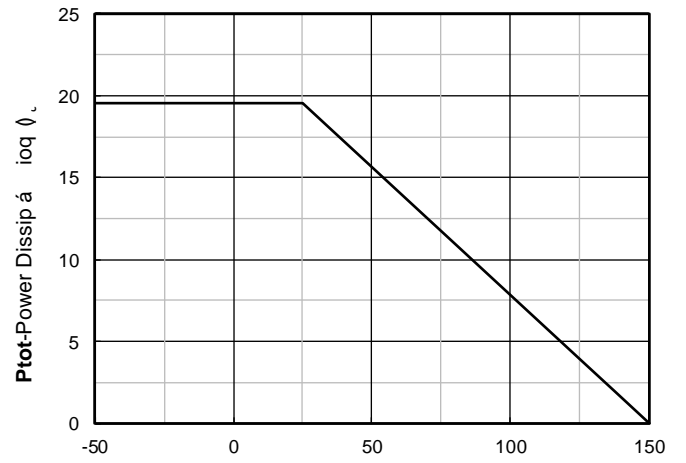
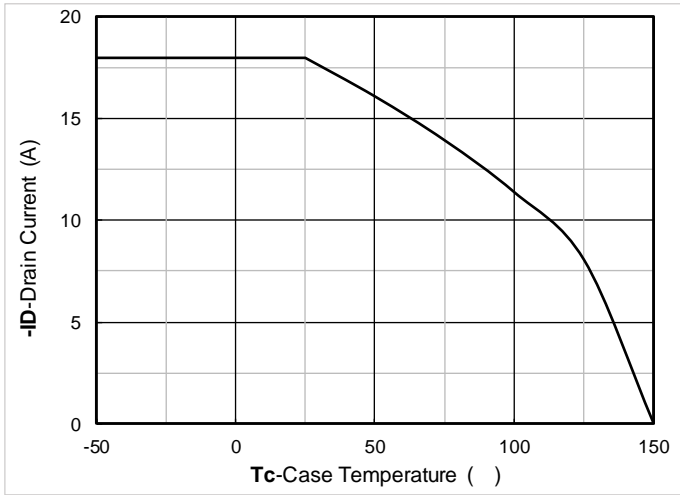


Figure 6. Normalized On-Resistance





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DFN3333-8L-B-0.8MM Package information

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.10\text{mm}$.
3. The pad layout is for reference purposes only.

Suggested Solder Pad Layout



Disclaimer

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with